Excellent Integrated System Limited

Stocking Distributor

Click to view price, real time Inventory, Delivery & Lifecycle Information:

<u>Vishay Semiconductor/Diodes Division</u> <u>VS-HFA90NH40PBF</u>

For any questions, you can email us directly: sales@integrated-circuit.com

Datasheet of VS-HFA90NH40PBF - DIODE MODULE 400V 210A D-67

Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com



VS-HFA90NH40PbF

Vishay Semiconductors

HEXFRED® Ultrafast Soft Recovery Diode, 210 A



	_		
НΔ	F-P	ΔΚ	(D-67)

PRODUCT SUMMARY					
I _F (maximum)	210 A				
V_{R}	400 V				
I _{F(DC)} at T _C	106 A at 100 °C				
Package	HALF-PAK (D-67)				
Circuit	Single diode				

FEATURES

- Very low Q_{rr} and t_{rr}
- · Designed and qualified for industrial level
- UL approved file E222165



• Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



BENEFITS

- · Reduced RFI and EMI
- · Reduced snubbing

DESCRIPTION

HEXFRED® diodes are optimized to reduce losses and EMI/RFI in high frequency power conditioning systems. An extensive characterization of the recovery behavior for different values of current, temperature and dI_F/dt simplifies the calculations of losses in the operating conditions. The softness of the recovery eliminates the need for a snubber in most applications. These devices are ideally suited for power converters, motors drives and other applications where switching losses are significant portion of the total losses.

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Cathode to anode voltage	V _R		400	V	
Continuous forward current	I_	T _C = 25 °C	210		
Continuous forward current	l _F	T _C = 100 °C	106	Α	
Single pulse forward current	I _{FSM}	Limited by junction temperature	600		
Non-repetitive avalanche energy	E _{AS}	$L = 100 \mu H$, duty cycle limited by maximum T_J	1.4	mJ	
Maximum power dissipation	В	T _C = 25 °C	329	W	
waxiinuin powei dissipation	P_{D}	T _C = 100 °C	132	VV	
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +150	°C	

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	V _{BR}	Ι _R = 100 μΑ		400	-	-	
		I _F = 90 A		-	1.06	1.45	V
Maximum forward voltage	V_{FM}	I _F = 180 A	See fig. 1 - 1	1.2	1.67		
		I _F = 90 A, T _J = 125 °C		-	0.96	1.23	
Maximum reverse leakage current	I _{RM}	T _J = 125 °C, V _R = 400 V See fig. 2		-	0.6	2	mA
Junction capacitance	C _T	$V_R = 200 \text{ V}$ See fig. 3		-	180	260	pF
Series inductance	L _S	From top of terminal hole to mounting plane		-	7.0	-	nH

Revision: 19-Mar-15 Document Number: 94044

Datasheet of VS-HFA90NH40PBF - DIODE MODULE 400V 210A D-67





VS-HFA90NH40PbF

Vishay Semiconductors

DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Reverse recovery time See fig. 5	t _{rr}	T _J = 25 °C	I _F = 90 A	-	90	140	ns
		T _J = 125 °C		-	158	240	
Peak recovery current See fig. 6	I _{RRM}	T _J = 25 °C		-	9	17	А
		T _J = 125 °C		-	15	30	
Reverse recovery charge See fig. 7	0	T _J = 25 °C	- dl _F /dt = 200 A/μs V _R = 200 V	-	420	1100	nC
	Q _{rr}	T _J = 125 °C		-	1200	3200	iiC
Peak rate of recovery current See fig. 8	of recovery current /	T _J = 25 °C		-	370	-	Λ /
	dl _{(rec)M} /dt	T _J = 125 °C		-	270	-	A/μs

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER		SYMBOL TEST CONDITIONS		VALUES	UNITS	
Maximum junction and storage temperature range	•	T _J , T _{Stg}		-55 to 150	°C	
Maximum thermal resistance, junction to case		R _{thJC}	DC operation See fig. 4	0.38		
Typical thermal resistance, case to heatsink		R _{thCS}	Mounting surface, flat, smooth and greased	0.05	°C/W	
Approximate weight				30	g	
				1.06	oz.	
Manustina tavana	minimum		Non-lubricated threads	3 (26.5)		
Mounting torque	maximum			4 (35.4)	N⋅m	
T 1	minimum			3.4 (30)	(lbf · in)	
Terminal torque	maximum			5 (44.2)	7	
Case style			HALF-PAK modu	ıle	•	

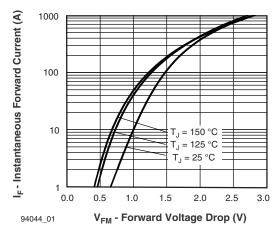


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

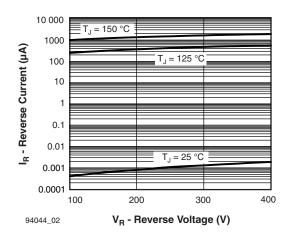


Fig. 2 - Typical Reverse Current vs. Reverse Voltage

Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com



www.vishay.com

VS-HFA90NH40PbF

Vishay Semiconductors

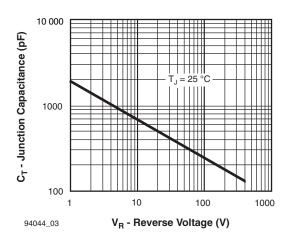


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

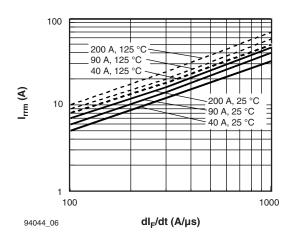


Fig. 6 - Typical Recovery Current vs. dl_F/dt

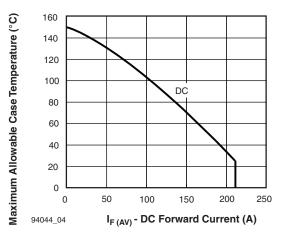


Fig. 4 - Maximum Allowable Case Temperature vs. DC Forward Current

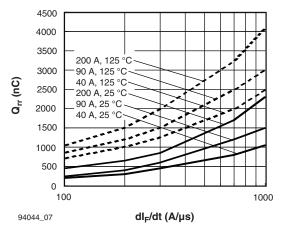


Fig. 7 - Typical Stored Charge vs. dI_F/dt

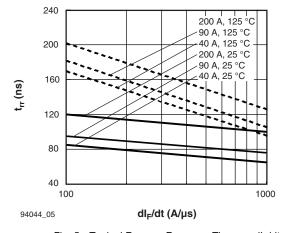


Fig. 5 - Typical Reverse Recovery Time vs. dI_F/dt

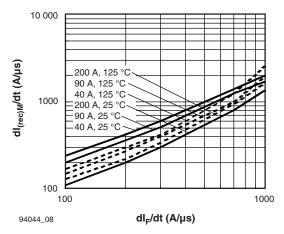


Fig. 8 - Typical $dI_{(rec)M}/dt$ vs. dI_F/dt

Datasheet of VS-HFA90NH40PBF - DIODE MODULE 400V 210A D-67

Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com

VS-HFA90NH40PbF



www.vishay.com

Vishay Semiconductors

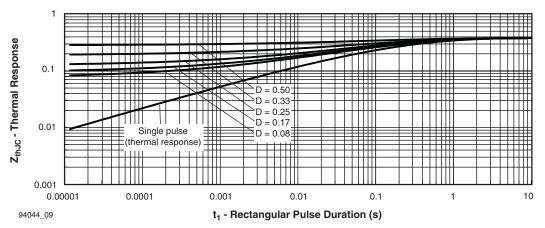


Fig. 9 - Maximum Thermal Impedance Z_{thJC} Characteristics (Per Leg)

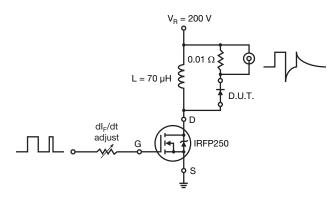
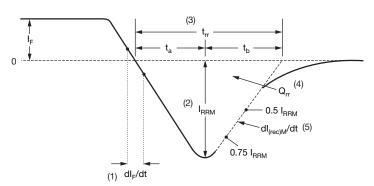


Fig. 10 - Reverse Recovery Parameter Test Circuit



- (1) dl_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.
- (4) $\mathbf{Q}_{\rm rr}$ area under curve defined by $\mathbf{t}_{\rm rr}$ and $\mathbf{I}_{\rm RRM}$
 - $Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$
- (5) $dI_{(rec)M}/dt$ peak rate of change of current during $t_{\rm b}$ portion of $t_{\rm rr}$

Fig. 11 - Reverse Recovery Waveform and Definitions

Datasheet of VS-HFA90NH40PBF - DIODE MODULE 400V 210A D-67
Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com



www.vishay.com

VS-HFA90NH40PbF

Vishay Semiconductors

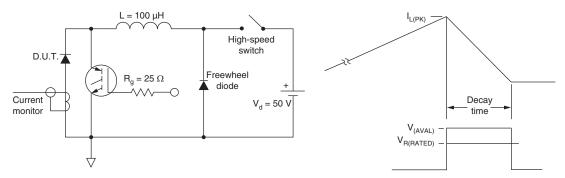
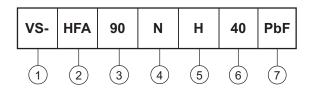


Fig. 12 - Avalanche Test Circuit and Waveforms

ORDERING INFORMATION TABLE

Device code



- 1 Vishay Semiconductors product
- 2 HEXFRED® family
- 3 Average current rating
- 4 N = Not isolated
- 5 H = HALF-PAK
- 6 Voltage rating (400 V)
- 7 Lead (Pb)-free

LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95020				

Datasheet of VS-HFA90NH40PBF - DIODE MODULE 400V 210A D-67



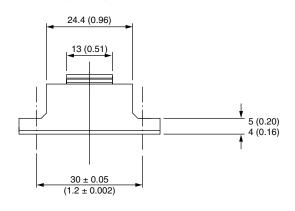


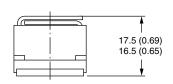
Outline Dimensions

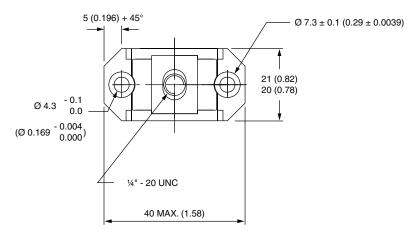
Vishay Semiconductors

D-67 HALF-PAK

DIMENSIONS in millimeters (inches)









Distributor of Vishay Semiconductor/Diodes Division: Excellent Integrated System Limite Datasheet of VS-HFA90NH40PBF - DIODE MODULE 400V 210A D-67

Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com

Legal Disclaimer Notice

VISHAY. W

www.vishay.com

Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

Revision: 13-Jun-16 1 Document Number: 91000